

Inverter Grade Thyristors (Hockey PUK Version), 720 A


TO-200AB (E-PUK)
FEATURES

- Metal case with ceramic insulator
- All diffused design
- Center amplifying gate
- Guaranteed high dV/dt
- Guaranteed high dI/dt
- International standard case TO-200AB (E-PUK)
- High surge current capability
- Low thermal impedance
- High speed performance
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912


**RoHS
COMPLIANT**

| PRODUCT SUMMARY | |
|--------------------|------------------|
| Package | TO-200AB (E-PUK) |
| Diode variation | Single SCR |
| $I_{T(AV)}$ | 720 A |
| V_{DRM}/V_{RRM} | 400 V, 800 V |
| V_{TM} | 1.96 V |
| I_{TSM} at 50 Hz | 11 000 A |
| I_{TSM} at 60 Hz | 11 500 A |
| I_{GT} | 200 mA |
| T_C/T_{hs} | 55 °C |

TYPICAL APPLICATIONS

- Inverters
- Choppers
- Induction heating
- All types of force-commutated converters

| MAJOR RATINGS AND CHARACTERISTICS | | | |
|-----------------------------------|-----------------|------------|-------------------|
| PARAMETER | TEST CONDITIONS | VALUES | UNITS |
| $I_{T(AV)}$ | | 720 | A |
| | T_{hs} | 55 | °C |
| $I_{T(RMS)}$ | | 1435 | A |
| | T_{hs} | 25 | °C |
| I_{TSM} | 50 Hz | 11 000 | A |
| | 60 Hz | 11 500 | |
| I^2t | 50 Hz | 605 | kA ² s |
| | 60 Hz | 553 | |
| V_{DRM}/V_{RRM} | | 400 to 800 | V |
| t_q | Range | 10 to 30 | μs |
| T_J | | -40 to 125 | °C |

ELECTRICAL SPECIFICATIONS

| VOLTAGE RATINGS | | | | |
|-----------------|--------------|--|--|--|
| TYPE NUMBER | VOLTAGE CODE | V_{DRM}/V_{RRM} , MAXIMUM REPETITIVE PEAK VOLTAGE V | V_{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V | I_{DRM}/I_{RRM} MAXIMUM AT $T_J = T_J$ MAXIMUM mA |
| VS-ST333C..C | 04 | 400 | 500 | 50 |
| | 08 | 800 | 900 | |



| CURRENT CARRYING CAPABILITY | | | | | | | |
|----------------------------------|-----------|------|-----------|------|-----------|------|----------------|
| FREQUENCY | | | | | | | UNITS |
| 50 Hz | 1630 | 1420 | 2520 | 2260 | 7610 | 6820 | A |
| 400 Hz | 1630 | 1390 | 2670 | 2330 | 4080 | 3600 | |
| 1000 Hz | 1350 | 1090 | 2440 | 2120 | 2420 | 2100 | |
| 2500 Hz | 720 | 550 | 1450 | 1220 | 1230 | 1027 | |
| Recovery voltage V_r | 50 | | 50 | | 50 | | V |
| Voltage before turn-on V_d | V_{DRM} | | V_{DRM} | | V_{DRM} | | |
| Rise of on-state current di/dt | 50 | | - | | - | | A/ μ s |
| Heatsink temperature | 40 | 55 | 40 | 55 | 40 | 55 | $^{\circ}$ C |
| Equivalent values for RC circuit | 10/0.47 | | 10/0.47 | | 10/0.47 | | Ω/μ F |

| ON-STATE CONDUCTION | | | | | | |
|--|---------------|--|---------------------------|---|-----------|----------------|
| PARAMETER | SYMBOL | TEST CONDITIONS | | | VALUES | UNITS |
| Maximum average on-state current at heatsink temperature | $I_{T(AV)}$ | 180° conduction, half sine wave Double side (single side) cooled | | | 720 (350) | A |
| | | | | | 55 (75) | $^{\circ}$ C |
| Maximum RMS on-state current | $I_{T(RMS)}$ | DC at 25 $^{\circ}$ C heatsink temperature double side cooled | | | 1435 | A |
| Maximum peak, one half cycle, non-repetitive surge current | I_{TSM} | t = 10 ms | No voltage reapplied | Sinusoidal half wave, initial $T_J = T_J$ maximum | 11 000 | |
| | | t = 8.3 ms | | | 11 500 | |
| | | t = 10 ms | 100 % V_{RRM} reapplied | | 9250 | |
| | | t = 8.3 ms | | | 9700 | |
| Maximum I^2t for fusing | I^2t | t = 10 ms | No voltage reapplied | Sinusoidal half wave, initial $T_J = T_J$ maximum | 605 | kA^2s |
| | | t = 8.3 ms | | | 553 | |
| | | t = 10 ms | 100 % V_{RRM} reapplied | | 428 | |
| | | t = 8.3 ms | | | 391 | |
| Maximum $I^2\sqrt{t}$ for fusing | $I^2\sqrt{t}$ | t = 0.1 to 10 ms, no voltage reapplied | | | 6050 | $kA^2\sqrt{s}$ |
| Maximum peak on-state voltage | V_{TM} | $I_{TM} = 1810$ A, $T_J = T_J$ maximum, $t_p = 10$ ms sine wave pulse | | | 1.96 | V |
| Low level value of threshold voltage | $V_{T(TO)1}$ | $(16.7 \% \times \pi \times I_{T(AV)}) < I < \pi \times I_{T(AV)}$, $T_J = T_J$ maximum | | | 0.91 | |
| High level value of threshold voltage | $V_{T(TO)2}$ | $I > \pi \times I_{T(AV)}$, $T_J = T_J$ maximum | | | 0.93 | |
| Low level value of forward slope resistance | r_{t1} | $(16.7 \% \times \pi \times I_{T(AV)}) < I < \pi \times I_{T(AV)}$, $T_J = T_J$ maximum | | | 0.58 | $m\Omega$ |
| High level value of forward slope resistance | r_{t2} | $I > \pi \times I_{T(AV)}$, $T_J = T_J$ maximum | | | 0.58 | |
| Maximum holding current | I_H | $T_J = 25$ $^{\circ}$ C, $I_T > 30$ A | | | 600 | mA |
| Typical latching current | I_L | $T_J = 25$ $^{\circ}$ C, $V_A = 12$ V, $R_a = 6$ Ω , $I_G = 1$ A | | | 1000 | |

| SWITCHING | | | | | |
|--|---------|--|--------|------|------------|
| PARAMETER | SYMBOL | TEST CONDITIONS | VALUES | | UNITS |
| | | | MIN. | MAX. | |
| Maximum non-repetitive rate of rise of turned on current | di/dt | $T_J = T_J$ maximum, $V_{DRM} = \text{Rated } V_{DRM}$; $I_{TM} = 2 \times di/dt$ | 1000 | | A/ μ s |
| Typical delay time | t_d | $T_J = 25$ $^{\circ}$ C, $V_{DM} = \text{Rated } V_{DRM}$; $I_{TM} = 50$ A DC, $t_p = 1$ μ s Resistive load, gate pulse: 10 V, 5 Ω source | 1.1 | | μ s |
| Maximum turn-off time | t_q | $T_J = T_J$ maximum, $I_{TM} = 550$ A, commutating $di/dt = 40$ A/ μ s $V_R = 50$ V, $t_p = 500$ μ s, dV/dt : See table in device code | 10 | 30 | |



| BLOCKING | | | | |
|--|--|--|--------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | VALUES | UNITS |
| Maximum critical rate of rise of off-state voltage | dV/dt | T _J = T _J maximum, linear to 80 % V _{DRM} , higher value available on request | 500 | V/μs |
| Maximum peak reverse and off-state leakage current | I _{RRM} , I _{DRM} | T _J = T _J maximum, rated V _{DRM} /V _{RRM} applied | 50 | mA |

| TRIGGERING | | | | |
|---|--------------------|---|--------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | VALUES | UNITS |
| Maximum peak gate power | P _{GM} | T _J = T _J maximum, f = 50 Hz, d% = 50 | 60 | W |
| Maximum average gate power | P _{G(AV)} | | 10 | |
| Maximum peak positive gate current | I _{GM} | T _J = T _J maximum, t _p ≤ 5 ms | 10 | A |
| Maximum peak positive gate voltage | + V _{GM} | | 20 | |
| Maximum peak negative gate voltage | - V _{GM} | | 5 | |
| Maximum DC gate current required to trigger | I _{GT} | T _J = 25 °C, V _A = 12 V, R _a = 6 Ω | 200 | mA |
| Maximum DC gate voltage required to trigger | V _{GT} | | 3 | |
| Maximum DC gate current not to trigger | I _{GD} | T _J = T _J maximum, rated V _{DRM} applied | 20 | mA |
| Maximum DC gate voltage not to trigger | V _{GD} | | 0.25 | |

| THERMAL AND MECHANICAL SPECIFICATIONS | | | | |
|--|---------------------|---|------------------|-----------|
| PARAMETER | SYMBOL | TEST CONDITIONS | VALUES | UNITS |
| Maximum operating temperature range | T _J | | -40 to 125 | °C |
| Maximum storage temperature range | T _{Stg} | | -40 to 150 | |
| Maximum thermal resistance, junction to heatsink | R _{thJ-hs} | DC operation single side cooled | 0.09 | K/W |
| | | DC operation double side cooled | 0.04 | |
| Maximum thermal resistance, case to heatsink | R _{thC-hs} | DC operation single side cooled | 0.020 | |
| | | DC operation double side cooled | 0.010 | |
| Mounting force, ± 10 % | | | 9800 (1000) | N (kg) |
| Approximate weight | | | 83 | g |
| Case style | | See dimensions - link at the end of datasheet | TO-200AB (E-PUK) | |

| ΔR_{thJ-hs} CONDUCTION | | | | | | |
|---------------------------------------|-----------------------|-------------|------------------------|-------------|---|-------|
| CONDUCTION ANGLE | SINUSOIDAL CONDUCTION | | RECTANGULAR CONDUCTION | | TEST CONDITIONS | UNITS |
| | SINGLE SIDE | DOUBLE SIDE | SINGLE SIDE | DOUBLE SIDE | | |
| 180° | 0.010 | 0.011 | 0.007 | 0.007 | T _J = T _J maximum | K/W |
| 120° | 0.012 | 0.012 | 0.012 | 0.013 | | |
| 90° | 0.015 | 0.015 | 0.016 | 0.017 | | |
| 60° | 0.022 | 0.022 | 0.023 | 0.023 | | |
| 30° | 0.036 | 0.036 | 0.036 | 0.037 | | |

Note

- The table above shows the increment of thermal resistance R_{thJ-hs} when devices operate at different conduction angles than DC

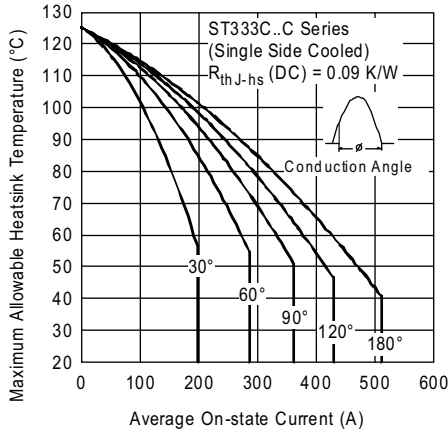


Fig. 1 - Current Ratings Characteristics

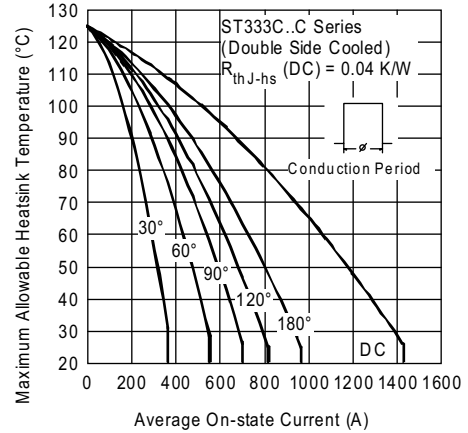


Fig. 4 - Current Ratings Characteristics

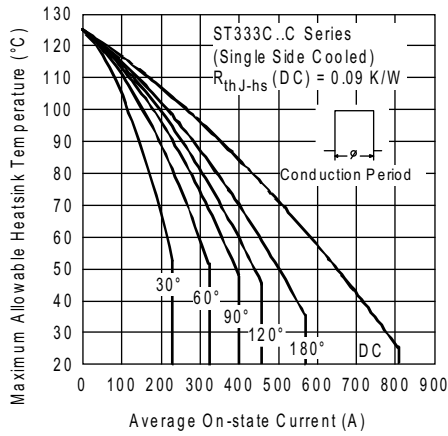


Fig. 2 - Current Ratings Characteristics

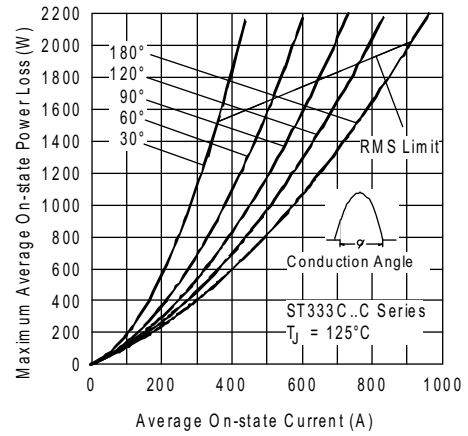


Fig. 5 - On-State Power Loss Characteristics

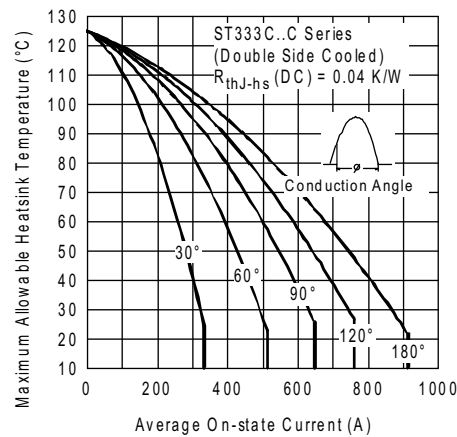


Fig. 3 - Current Ratings Characteristics

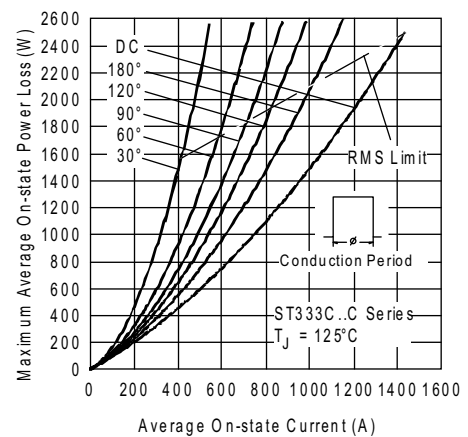


Fig. 6 - On-State Power Loss Characteristics



Fig. 7 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

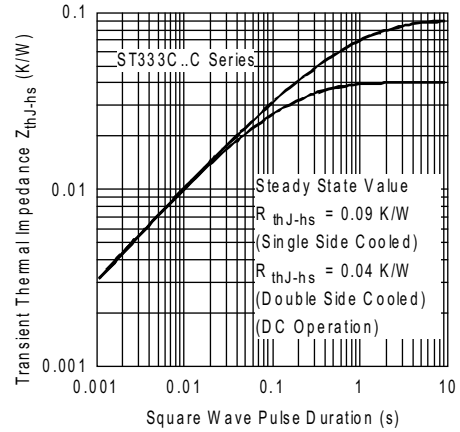


Fig. 10 - Thermal Impedance Z_{thJ-hs} Characteristics



Fig. 8 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

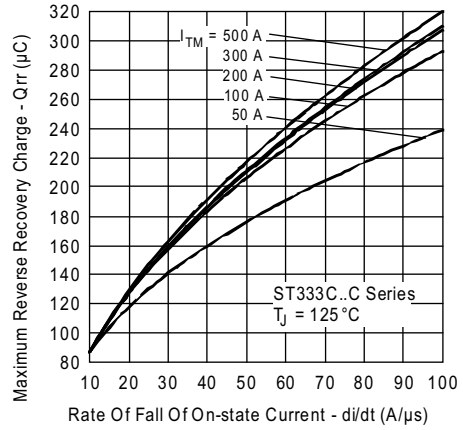


Fig. 11 - Reverse Recovered Charge Characteristics



Fig. 9 - On-State Voltage Drop Characteristics

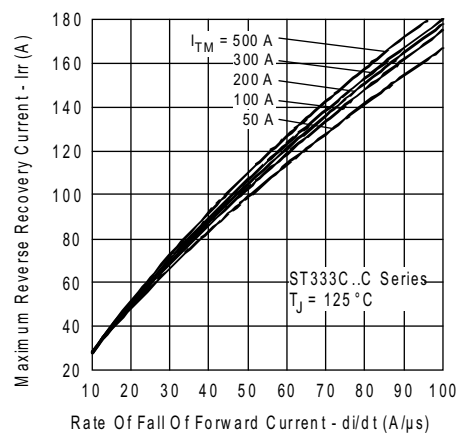


Fig. 12 - Reverse Recovery Current Characteristics

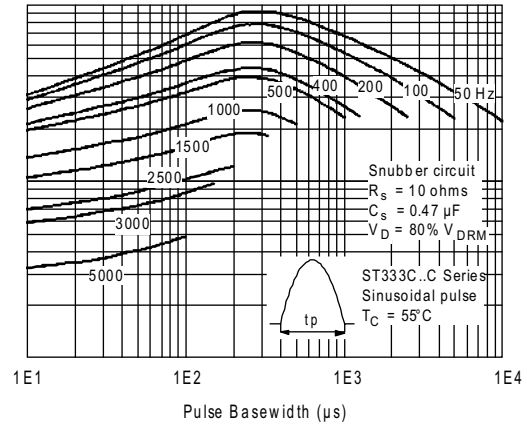
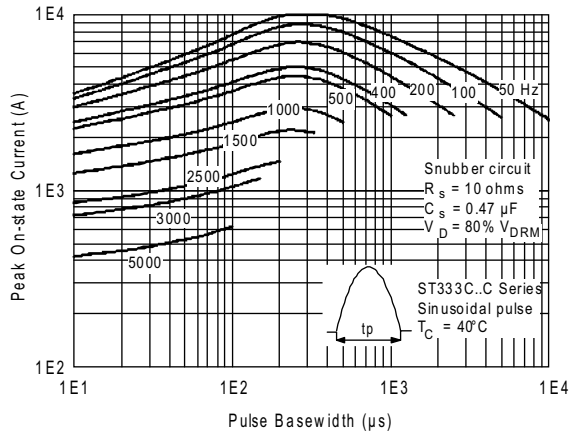


Fig. 13 - Frequency Characteristics

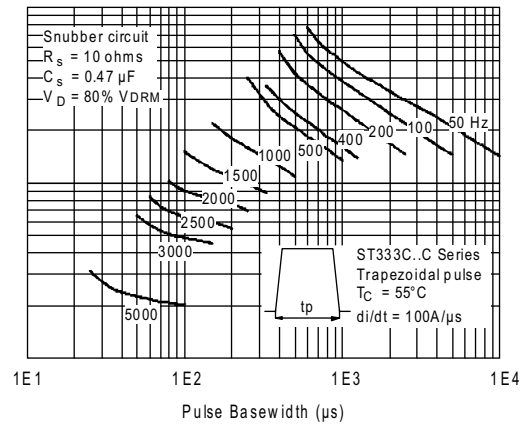
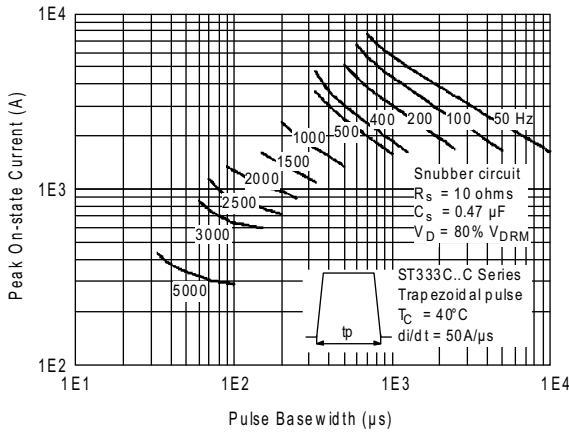


Fig. 14 - Frequency Characteristics

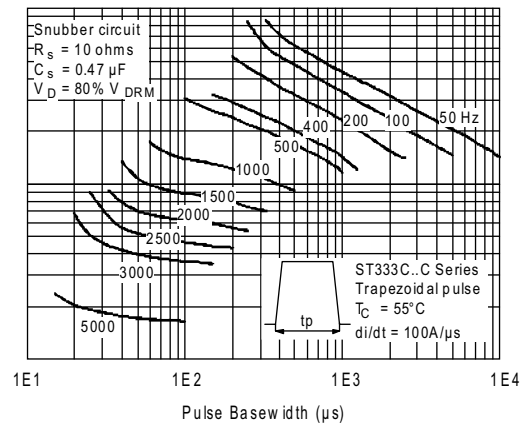
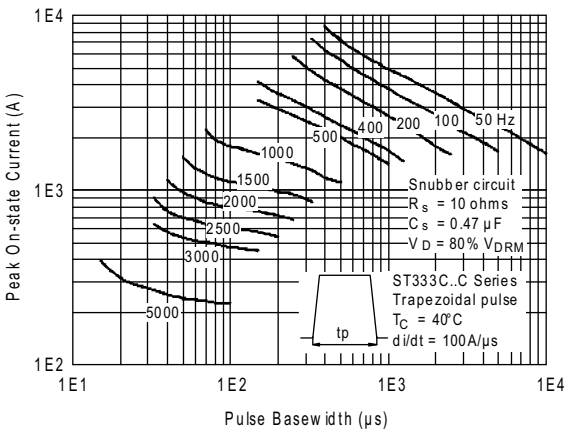


Fig. 15 - Frequency Characteristics



Fig. 16 - Maximum On-State Energy Power Loss Characteristics



Fig. 17 - Gate Characteristics



ORDERING INFORMATION TABLE

| | | | | | | | | | | | |
|-------------|------------|-----------|-----------|----------|----------|-----------|----------|----------|----------|----------|----------|
| Device code | VS- | ST | 33 | 3 | C | 08 | C | H | K | 1 | - |
| | ① | ② | ③ | ④ | ⑤ | ⑥ | ⑦ | ⑧ | ⑨ | ⑩ | ⑪ |

- 1** - Vishay Semiconductors product
- 2** - Thyristor
- 3** - Essential part number
- 4** - 3 = Fast turn off
- 5** - C = Ceramic PUK
- 6** - Voltage code x 100 = V_{RRM} (see Voltage Ratings table)
- C = PUK case TO-200AB (E-PUK)
- 7** - Reapplied dV/dt code (for t_q test condition)
- 8** - t_q code
- 9** - 0 = Eyelet term.
- 10** - (gate and aux. cathode unsoldered leads)
1 = Fast-on term.
(gate and aux. cathode unsoldered leads)
2 = Eyelet term.
(gate and aux. cathode soldered leads)
3 = Fast-on term.
(gate and aux. cathode soldered leads)
- 11** - Critical dV/dt:
 - None = 500 V/ μ s (standard value)
 - L = 1000 V/ μ s (special selection)

| dV/dt - t_q combinations available | | | | | |
|--------------------------------------|----|----|-----|------------|-----|
| dV/dt (V/ μ s) | 20 | 50 | 100 | 200 | 400 |
| 10 | CN | DN | EN | -- | -- |
| 12 | CM | DM | EM | FM* | -- |
| 15 | CL | DL | EL | FL* | HL |
| 18 | CP | DP | EP | FP | HP |
| 20 | CK | DK | EK | FK | HK |
| 25 | -- | -- | -- | FJ | HJ |
| 30 | -- | -- | -- | -- | HH |

* Standard part number.
All other types available only on request.

| LINKS TO RELATED DOCUMENTS | |
|----------------------------|---|
| Dimensions | http://www.vishay.com/doc?95075 |

TO-200AB (E-PUK)

DIMENSIONS in millimeters (inches)

Anode to gate
 Creepage distance: 11.18 (0.44) minimum
 Strike distance: 7.62 (0.30) minimum



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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- Поставку компонентов в любых объемах, удовлетворяющих вашим потребностям.
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